

Amendments to the Claims

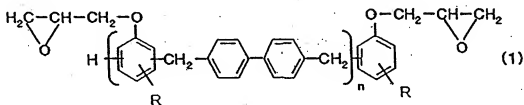
This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Please amend the claims as follows:

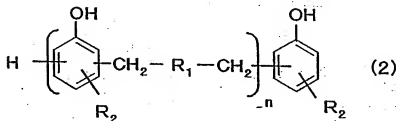
1. (Currently Amended) A resin composition for encapsulating a semiconductor chip comprising:

an epoxy resin (A) represented by general formula (1):



wherein R represents hydrogen or alkyl having up to four carbon atoms; and n is a positive number from 4 to 10 0.5 to 5 as an average;

a phenol resin (B) represented by general formula (2):



wherein R_1 represents phenylene or biphenylene; R_2 represents hydrogen or alkyl having up to four carbon atoms; and n is a positive number from ~~1 to 10~~ 0.5 to 5 as an average;

an inorganic filler (C);

a curing accelerator (D);

a silane coupling agent (E); and

Compound (F) containing two and more hydroxyl groups on adjacent carbon atoms in naphthalene ring.

2. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said Compound (F) in more than or equal to 0.01 wt%.

3. (Original) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein the resin composition comprises said silane coupling agent (E) in 0.01 wt% to 1 wt% both inclusive.

4.-5. (Cancelled)

6. (Previously Presented) The resin composition for encapsulating a semiconductor chip according to Claim 1, wherein said Compound (F) contains two hydroxyl groups on adjacent carbon atoms in said naphthalene ring.

7. (Original) The resin composition for encapsulating a semiconductor chip according to Claims 1, wherein the resin composition comprises said inorganic filler (C) in 84 wt% to 90 wt% both inclusive.

8. (Previously Presented) A semiconductor device wherein a semiconductor chip is encapsulated by the resin composition according to Claim 1.

9. (Previously Presented) The resin composition for encapsulating a semiconductor chip according to Claim 1,

wherein said inorganic filler (C) is present in an amount of 84 wt% to 90 wt% both inclusive,

said silane coupling agent (E) is present in an amount of 0.01 wt% to 1 wt% both inclusive, and

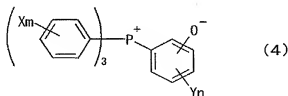
said Compound (F) is present in an amount of 0.01 wt% to 0.5 wt% both inclusive.

10. (Currently Amended) The resin composition for encapsulating a semiconductor chip according to Claim 1,

wherein said curing accelerator is a compound represented by general formula (3) and/or (4);



wherein P is phosphorous; R_1 , R_2 , R_3 and R_4 are substituted or unsubstituted aromatic or alkyl; A is an anion of an aromatic organic acid having a function group selected from the group consisting of hydroxyl, carboxyl and thiol in the aromatic ring; AH is an aromatic organic acid having at least one selected from hydroxyl, carboxyl and thiol in the aromatic ring; a and b are an integer of 1 to 3 both inclusive; and c is an integer of 0 to 3 both inclusive, provided that $a = b$;



wherein X is hydrogen or alkyl having 1 to 3 carbon atoms both inclusive; Y is hydrogen or hydroxyl; m and n are an integer of 1 to 3 both inclusive.